

SHINDENGEN

General Purpose Rectifiers

Dual

S1ZA60

600V 1.1A

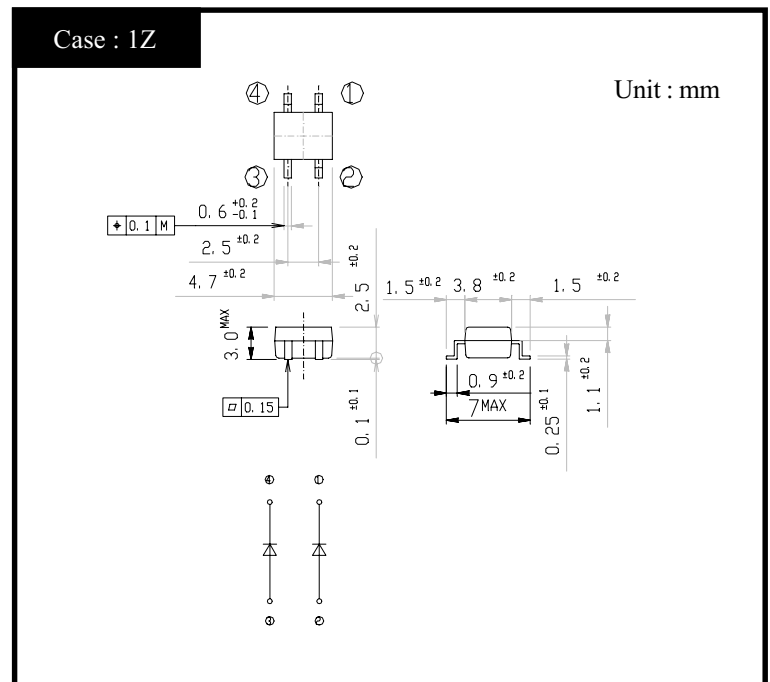
FEATURES

- Small SMT package
- Array
- High reliability with superior moisture resistance
- Applicable to Automatic Insertion

APPLICATION

- Conventional Rectification
- Motor
- Home Appliances, Office Equipment
- Telecommunication, Factory Automation

OUTLINE DIMENSIONS



RATINGS

● Absolute Maximum Ratings (If not specified Tl=25°C)

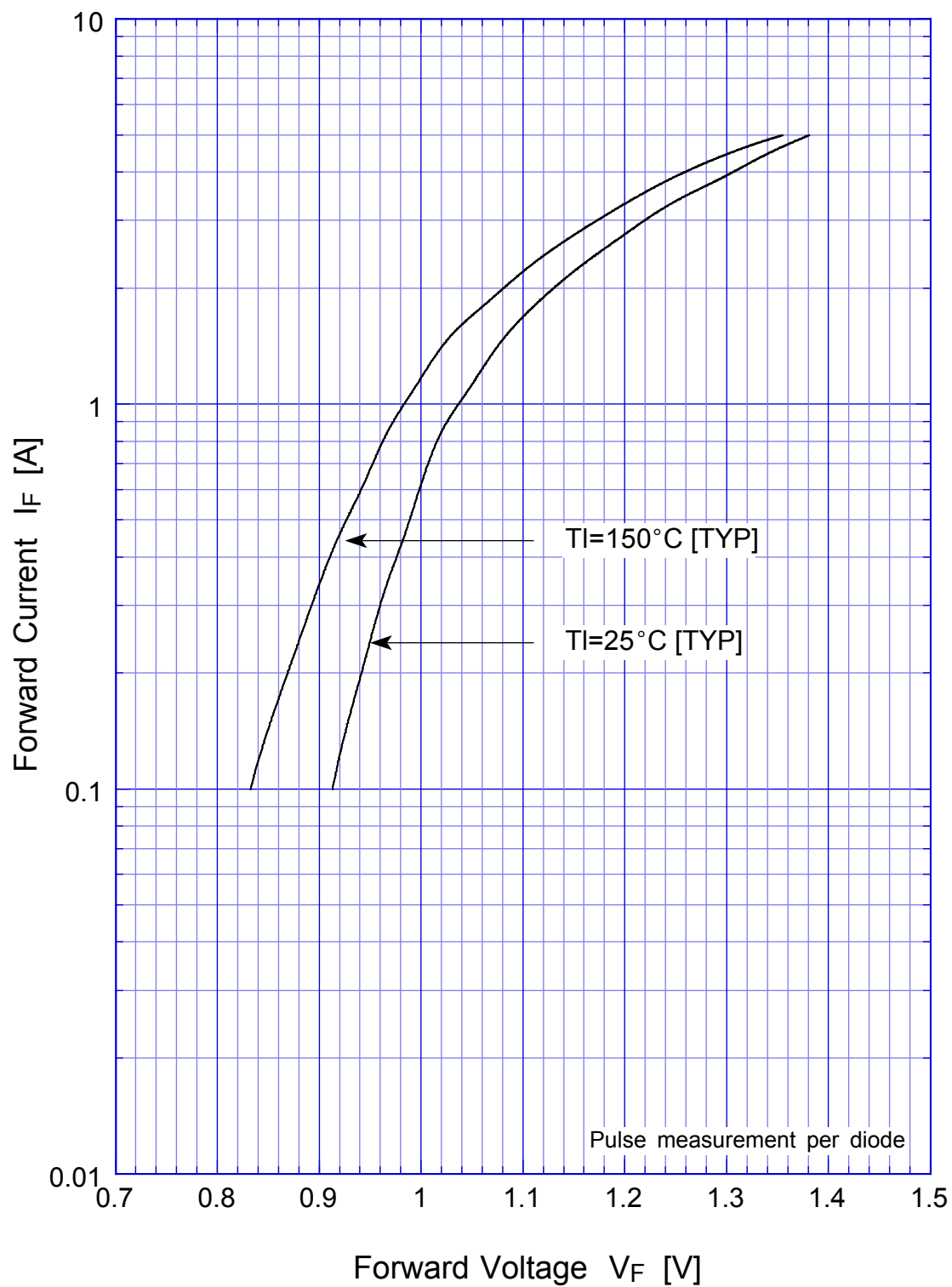
| Item | Symbol | Conditions | Ratings | Unit |
|-----------------------------------|------------------|---|---------|------|
| Storage Temperature | T _{stg} | | -40~150 | °C |
| Operating Junction Temperature | T _j | | 150 | °C |
| Maximum Reverse Voltage | V _{RM} | | 600 | V |
| Average Rectified Forward Current | I _O | 50Hz sine wave, R-load, T _a =25°C On alumina substrate 1 element operation | 1.1 | A |
| | | 50Hz sine wave, R-load, T _a =25°C On alumina substrate 2 element operation | 0.8 | |
| | | 50Hz sine wave, R-load, T _a =25°C On glass-epoxy substrate 1 element operation | 0.9 | |
| | | 50Hz sine wave, R-load, T _a =25°C On glass-epoxy substrate 2 element operation | 0.63 | |
| Peak Surge Forward Current | I _{FSM} | 50Hz sine wave, Non-repetitive 1cycle peak value, T _j =25°C | 30 | A |

● Electrical Characteristics (If not specified Tl=25°C)

| Item | Symbol | Conditions | Ratings | Unit |
|--------------------|-----------------|--|---------|------|
| Forward Voltage | V _F | I _F =0.9A, Pulse measurement, Rating of per diode | Max.1.1 | V |
| Reverse Current | I _R | V _R =V _{RM} , Pulse measurement, Rating of per diode | Max.10 | μA |
| Thermal Resistance | θ _{ja} | junction to ambient On alumina substrate 1 element operation | Max.93 | °C/W |
| | | junction to ambient On alumina substrate 2 element operation | Max.140 | |
| | | junction to ambient On glass-epoxy substrate 1 element operation | Max.120 | |
| | | junction to ambient On glass-epoxy substrate 2 element operation | Max.186 | |

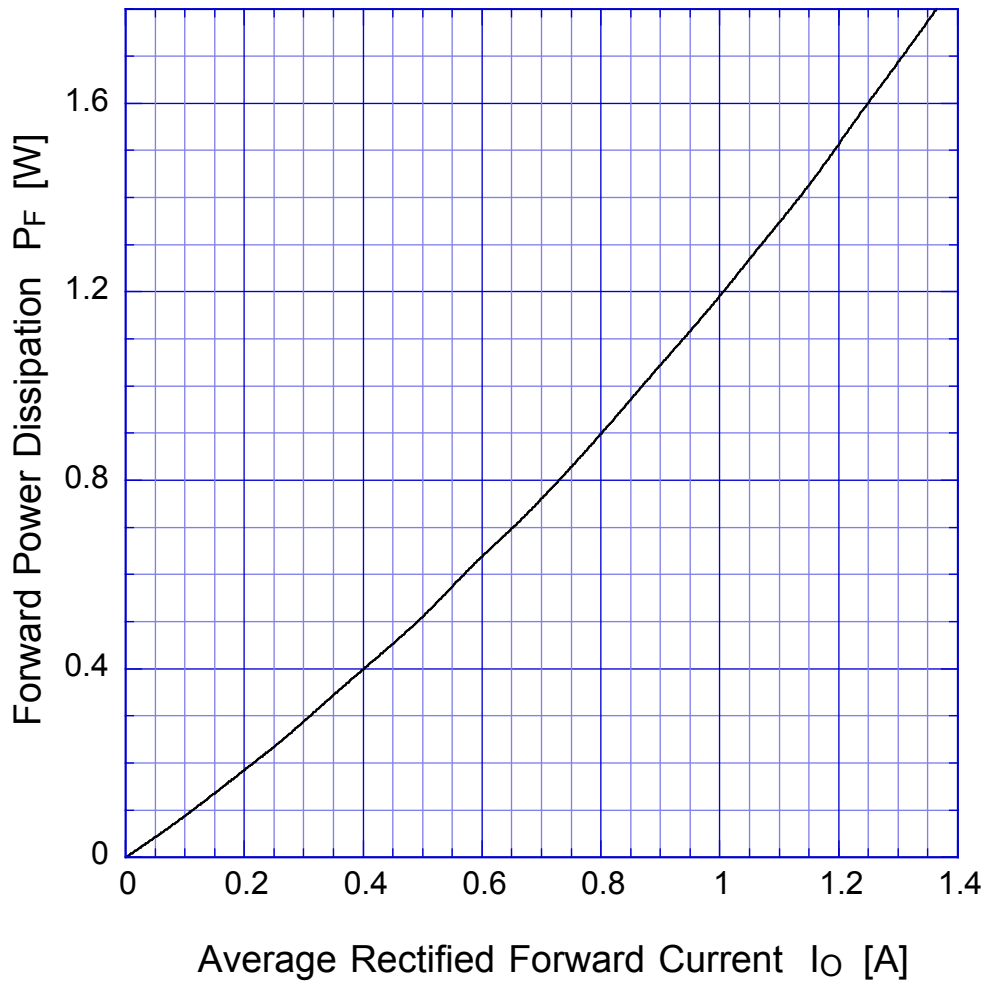
S1ZAx

Forward Voltage



S1ZAx

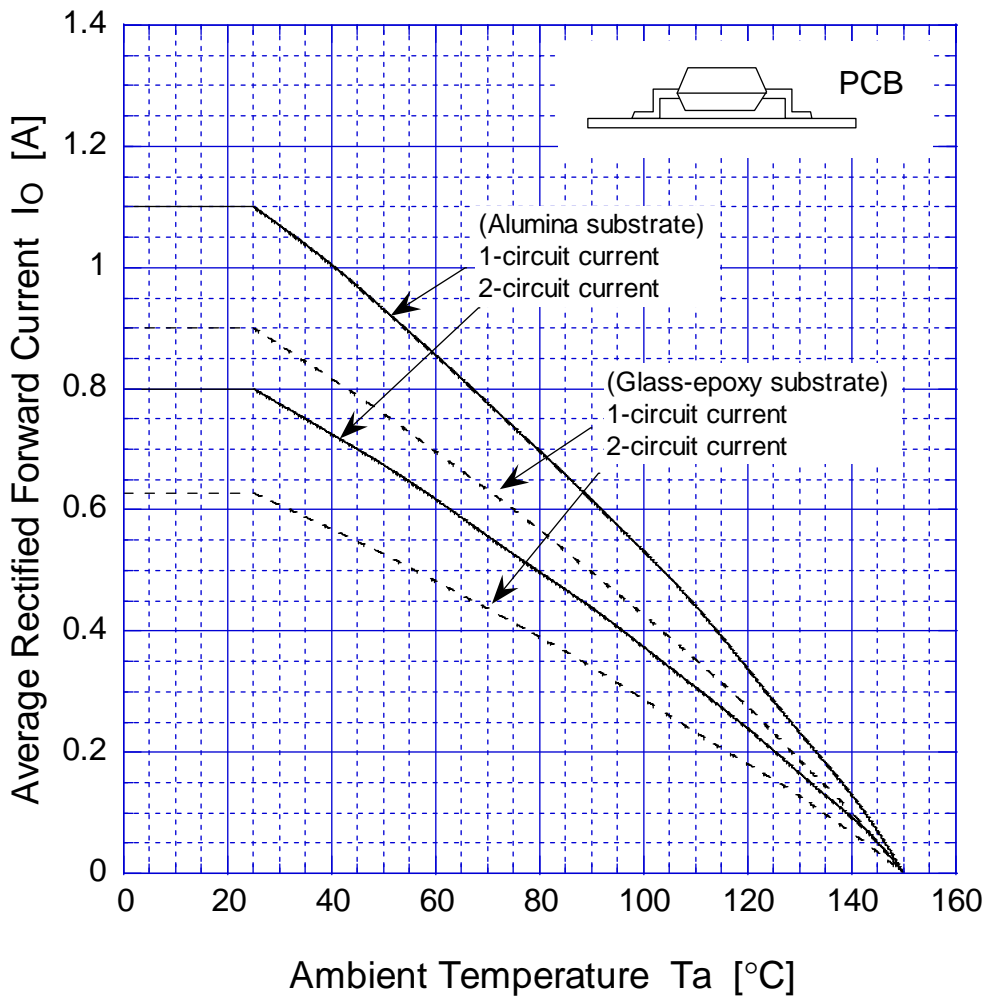
Forward Power Dissipation



$T_j = 150^\circ\text{C}$
Sine wave

S1ZAx

Derating Curve



Alumina substrate
Soldering land 1mm×1mm
Conductor layer 20 μ m
Substrate thickness 0.64mm

Glass-epoxy substrate
Soldering land 1mm×1mm
Conductor layer 35 μ m

Sine wave
R-load
Free in air

S1ZAx

Peak Surge Forward Capability

